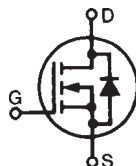


TrenchMV™ Power MOSFET

IXTA180N10T
IXTP180N10T

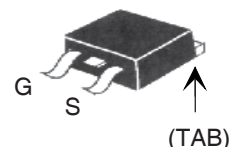
N-Channel Enhancement Mode
Avalanche Rated



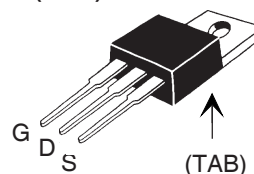
$$\begin{aligned} V_{DSS} &= 100V \\ I_{D25} &= 180A \\ R_{DS(on)} &\leq 6.4m\Omega \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C to } 175^\circ\text{C}$	100	V
V_{DGR}	$T_J = 25^\circ\text{C to } 175^\circ\text{C}, R_{GS} = 1M\Omega$	100	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	180	A
I_{LRMS}	Lead Current limit, RMS	75	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	450	A
I_{AR}	$T_C = 25^\circ\text{C}$	25	A
E_{AS}	$T_C = 25^\circ\text{C}$	750	mJ
P_D	$T_C = 25^\circ\text{C}$	480	W
T_J		-55 ... +175	$^\circ\text{C}$
T_{JM}		175	$^\circ\text{C}$
T_{stg}		-55 ... +175	$^\circ\text{C}$
T_L	1.6mm (0.062in.) from case for 10s	300	$^\circ\text{C}$
T_{SOLD}	Plastic body for 10 seconds	260	$^\circ\text{C}$
M_d	Mounting torque (TO-220)	1.13/10	Nm/lb.in
Weight	TO-263	2.5	g
	TO-220	3.0	g

TO-263 (IXTA)



TO-220 (IXTP)



G = Gate D = Drain
S = Source TAB = Drain

Features

- Ultra-low On Resistance
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect
- 175 $^\circ\text{C}$ Operating Temperature

Advantages

- Easy to mount
- Space savings
- High power density

Applications

- Automotive
 - Motor Drives
 - 42V Power Bus
 - ABS Systems
- DC/DC Converters and Off-line UPS
- Primary Switch for 24V and 48V Systems
- Distributed Power Architectures and VRMs
- Electronic Valve Train Systems
- High Current Switching Applications
- High Voltage Synchronous Rectifier

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	100		V
$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.5		4.5 V
I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}$			5 μA
	$V_{GS} = 0V, T_J = 150^\circ\text{C}$			100 μA
$R_{DS(on)}$	$V_{GS} = 10V, I_D = 25A$, Notes 1, 2		5.7	6.4 m Ω

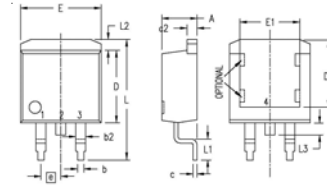
Symbol	Test Conditions	Characteristic Values		
(T _J = 25°C unless otherwise specified)		Min.	Typ.	Max.
g_{fs}	V _{DS} = 10V, I _D = 60A, Note 1	70	110	S
C_{iss}	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz		6900	pF
C_{oss}			923	pF
C_{rss}			162	pF
t_{d(on)}	Resistive Switching Times V _{GS} = 10V, V _{DS} = 0.5 • V _{DSS} , I _D = 25A R _G = 3.3Ω (External)		33	ns
t_r			54	ns
t_{d(off)}			42	ns
t_f			31	ns
Q_{g(on)}	V _{GS} = 10V, V _{DS} = 0.5 • V _{DSS} , I _D = 25A		151	nC
Q_{gs}			39	nC
Q_{gd}			45	nC
R_{thJC}	TO-220		0.50	0.31 °C/W
R_{thCH}				°C/W

Source-Drain Diode

Symbol	Test Conditions (T _J = 25°C unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
I _S	V _{GS} = 0V			180 A
I _{SM}	Repetitive, pulse width limited by T _{JM}			450 A
V _{SD}	I _F = 25A, V _{GS} = 0V, Note 1			0.95 V
t _{rr}	I _F = 90A, V _{GS} = 0V -di/dt = 100A/μs V _R = 0.5 • V _{DSS}		72	ns
I _{RM}			5.1	A
Q _{RM}			0.18	μC

- Notes: 1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.
2. On through-hole packages, R_{DS(on)} Kelvin test contact location must be 5mm or less from the package body.

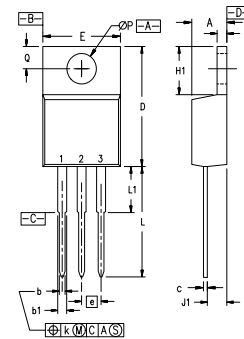
TO-263 (IXTA) Outline



Pins: 1 - Gate 2 - Drain
3 - Source 4, TAB - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.06	4.83	.160	.190
A1	2.03	2.79	.080	.110
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.46	0.74	.018	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	7.11	8.13	.280	.320
E	9.65	10.29	.380	.405
E1	6.86	8.13	.270	.320
e	2.54	BSC	.100	BSC
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.38	0	.015
R	0.46	0.74	.018	.029

TO-220 (IXTP) Outline



Pins: 1 - Gate 2 - Drain
3 - Source 4, TAB - Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

IXYS reserves the right to change limits, test conditions, and dimensions.

Fig. 1. Output Characteristics
@ 25°C

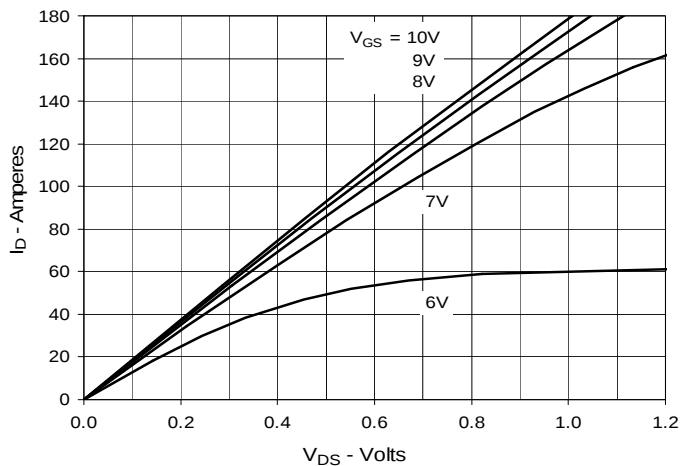


Fig. 2. Extended Output Characteristics
@ 25°C

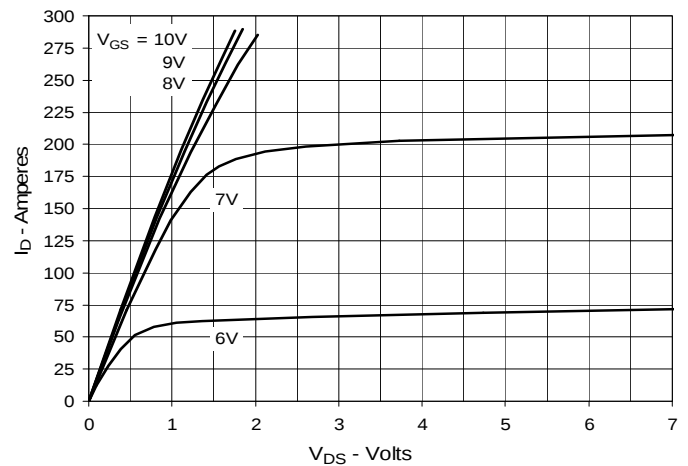


Fig. 3. Output Characteristics
@ 150°C

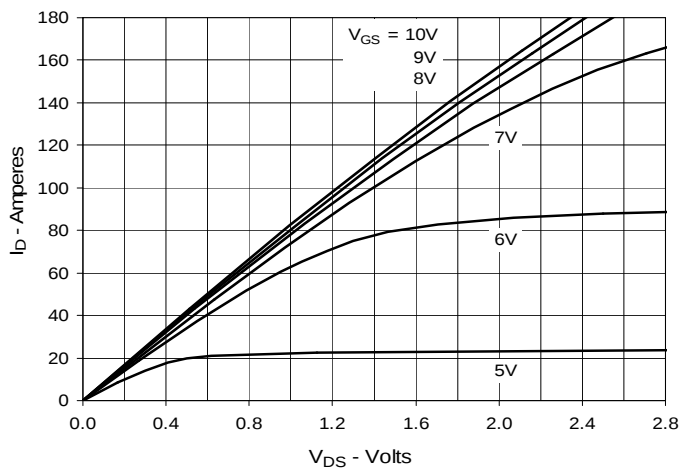


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 90A$ Value
vs. Junction Temperature

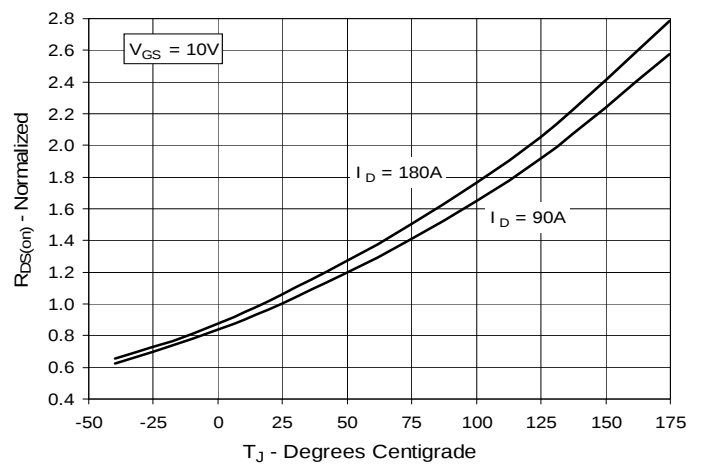


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 90A$ Value
vs. Drain Current

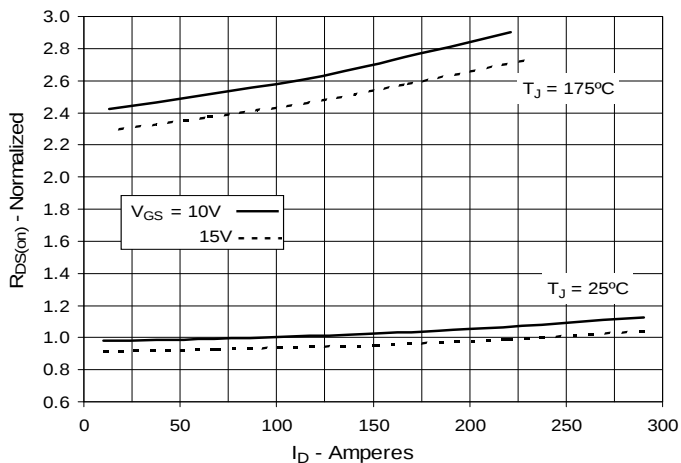


Fig. 6. Drain Current vs. Case Temperature

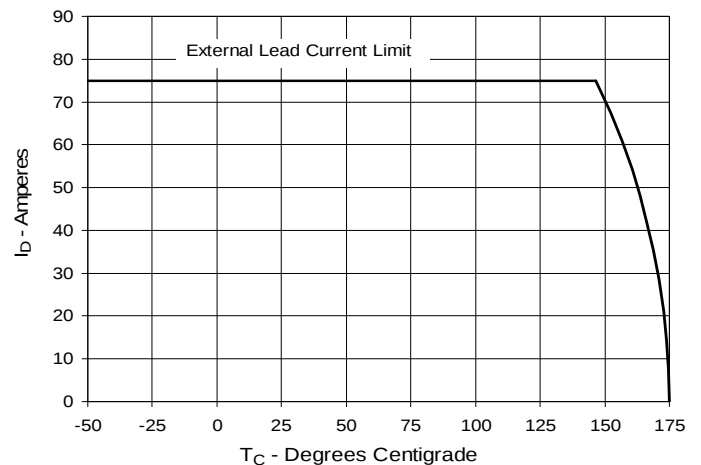


Fig. 7. Input Admittance

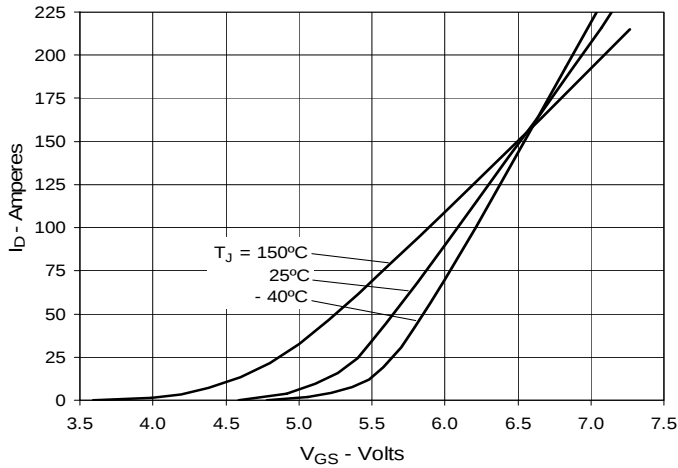


Fig. 8. Transconductance

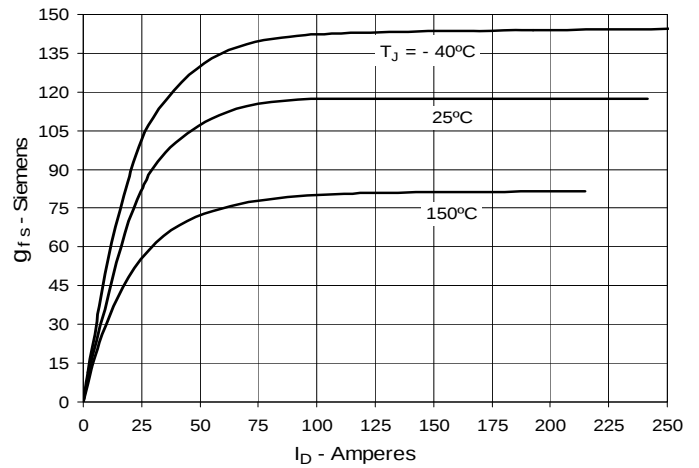


Fig. 9. Forward Voltage Drop of Intrinsic Diode

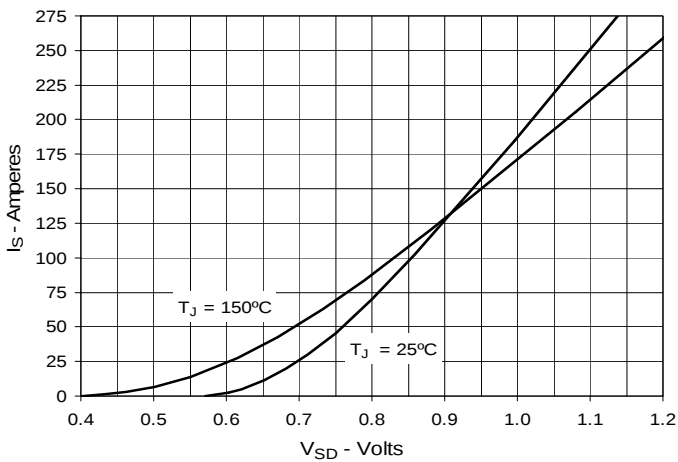


Fig. 10. Gate Charge

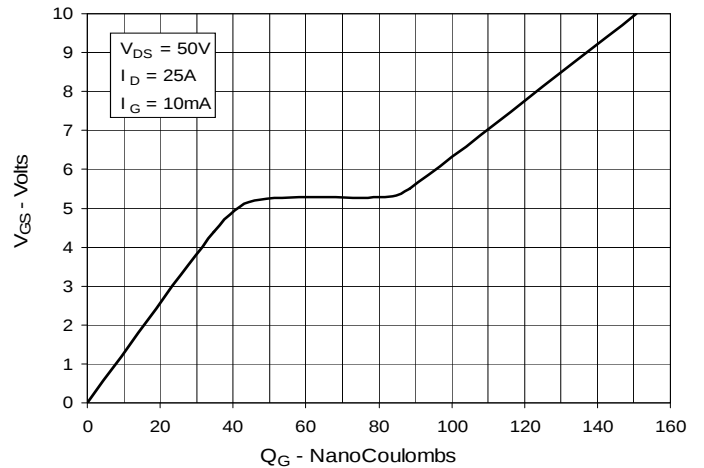


Fig. 11. Capacitance

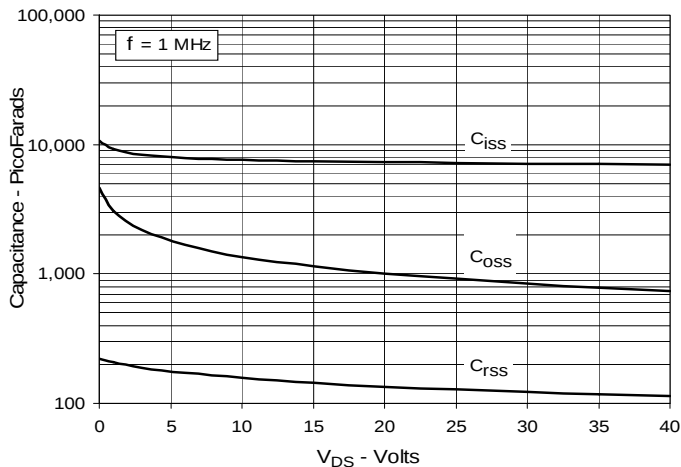
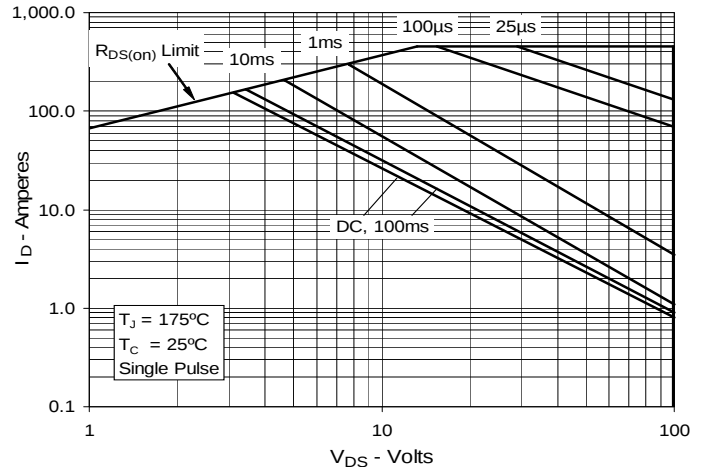
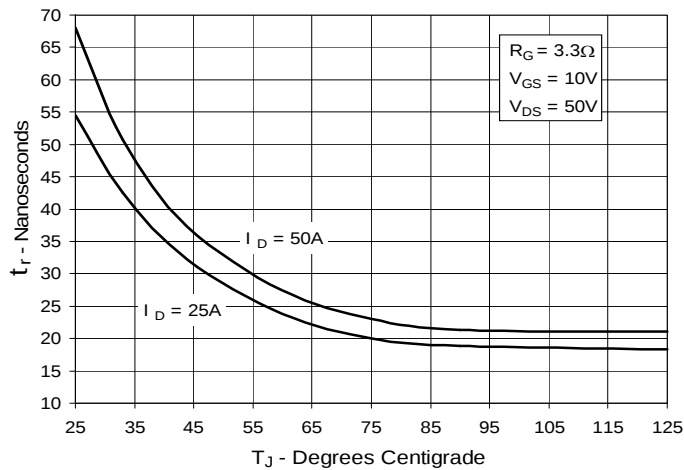


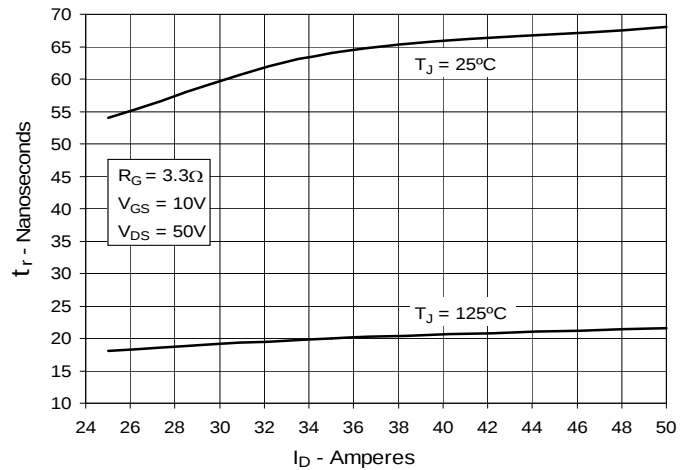
Fig. 12. Forward-Bias Safe Operating Area



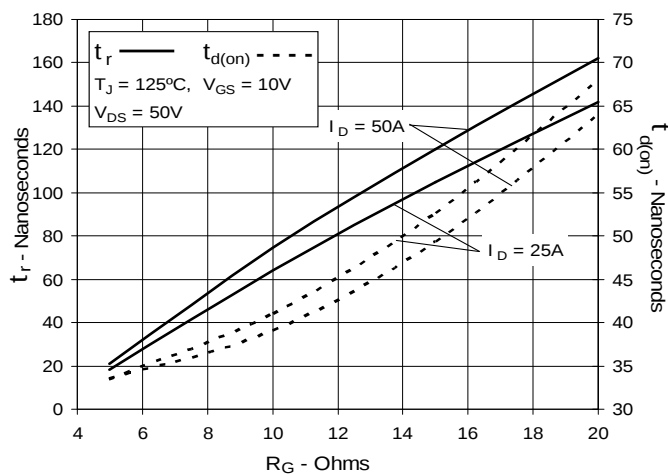
**Fig. 13. Resistive Turn-on
Rise Time vs. Junction Temperature**



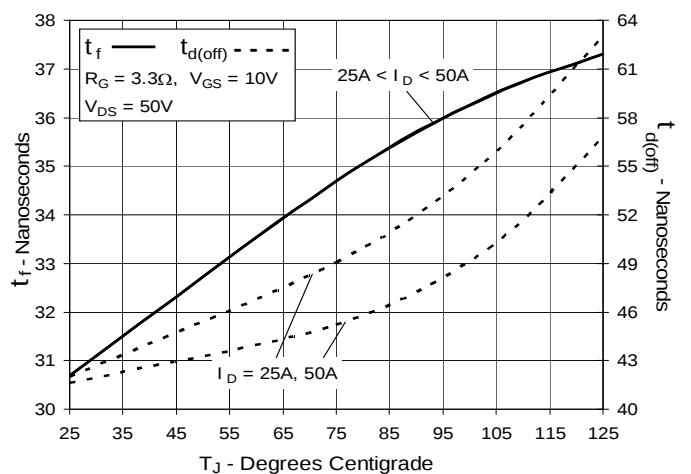
**Fig. 14. Resistive Turn-on
Rise Time vs. Drain Current**



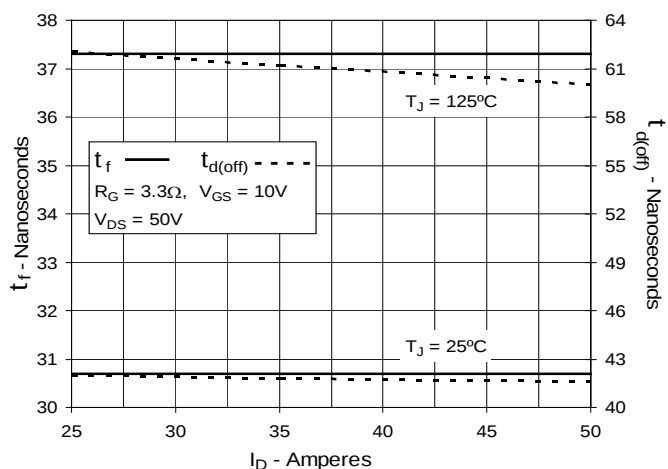
**Fig. 15. Resistive Turn-on
Switching Times vs. Gate Resistance**



**Fig. 16. Resistive Turn-off
Switching Times vs. Junction Temperature**



**Fig. 17. Resistive Turn-off
Switching Times vs. Drain Current**



**Fig. 18. Resistive Turn-off
Switching Times vs. Gate Resistance**

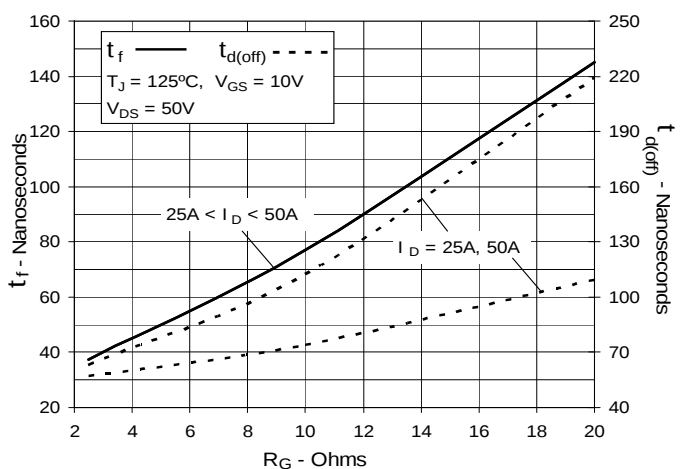


Fig. 19. Maximum Transient Thermal Impedance

